OPTO-ÉLECTRONIQUE

Travaux Pratiques

Semestre 5

Documentations techniques

— SFH206K
— LED Rouge
— TL081

Les documentations techniques sont disponibles sur le site des constructeurs.

Radial Sidelooker

SFH 206 K

Silicon PIN Photodiode

Applications

- Access Control & Security
- Appliances & Tools

Features

- Package: clear epoxy
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)
- Especially suitable for applications from 400 nm to 1100 nm
- Short switching time (typ. 20 ns)
- 5 mm LED plastic package
- Also available on tape and reel

Maximum Ratings

T_A = 25 °C

Parameter	Symbol		Values
Operating Temperature	T_{op}	min. max.	-40 °C 100 °C
Storage temperature	T_{stg}	min. max.	-40 °C 100 °C
Reverse voltage	V_R	max.	32 V
Total power dissipation	P_{tot}	max.	150 mW
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)	V_{ESD}	max.	2 kV

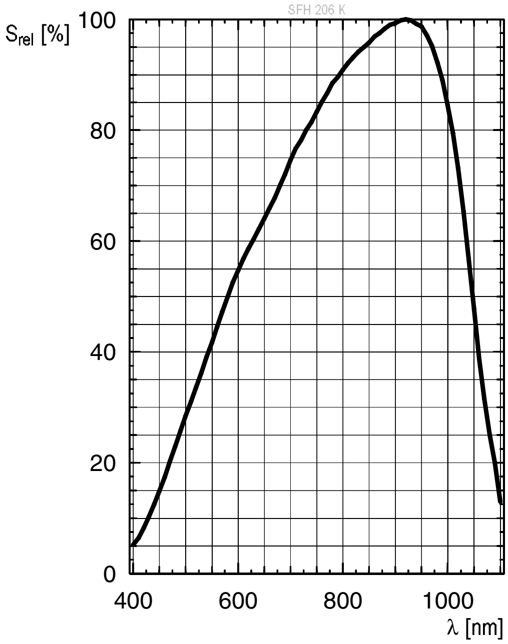
Characteristics

T_A = 25 °C

Parameter	Symbol		Values
Spectral sensitivity V_R = 5 V; Std. Light A; T = 2856 K	S	min. typ.	50 nA/lx 80 nA/lx
Wavelength of max sensitivity	$\lambda_{S\ max}$	typ.	920 nm
Spectral range of sensitivity	$\lambda_{10\%}$	typ.	420 ... 1120 nm
Radiant sensitive area	A	typ.	7.02 mm²
Dimensions of active chip area	L x W	typ.	2.65 x 2.65 mm x mm
Half angle	φ	typ.	60 °
Dark current V_R = 10 V	I_R	typ. max.	2 nA 30 nA
Spectral sensitivity of the chip λ = 850 nm	S_λ	typ.	0.62 A / W
Quantum yield of the chip λ = 850 nm	η	typ.	0.90 Electrons / Photon
Open-circuit voltage E_v = 1000 lx; Std. Light A; V_R = 0 V	V_O	min. typ.	310 mV 365 mV
Short-circuit current E_v = 1000 lx; Std. Light A; V_R = 0 V	I_{SC}	typ.	80 µA
Rise time V_R = 5 V; R_L = 50 Ω; λ = 850 nm; I_P = 800 µA	t_r	typ.	0.02 µs
Fall time V_R = 5 V; R_L = 50 Ω; λ = 850 nm; I_P = 800 µA	t_f	typ.	0.02 µs
Forward voltage I_F = 100 mA; E = 0	V_F	typ.	1.3 V
Capacitance V_R = 0 V; f = 1 MHz; E = 0	C_0	typ.	72 pF
Temperature coefficient of voltage	TC_V	typ.	-2.6 mV / K
Temperature coefficient of short-circuit current Std. Light A	TC_I	typ.	0.18 % / K
Noise equivalent power V_R = 10 V; λ = 850 nm	NEP	typ.	0.041 pW / $Hz^{1/2}$
Detection limit V_R = 10 V; λ = 850 nm	D*	typ.	6.5e12 cm x $Hz^{1/2}$ / W

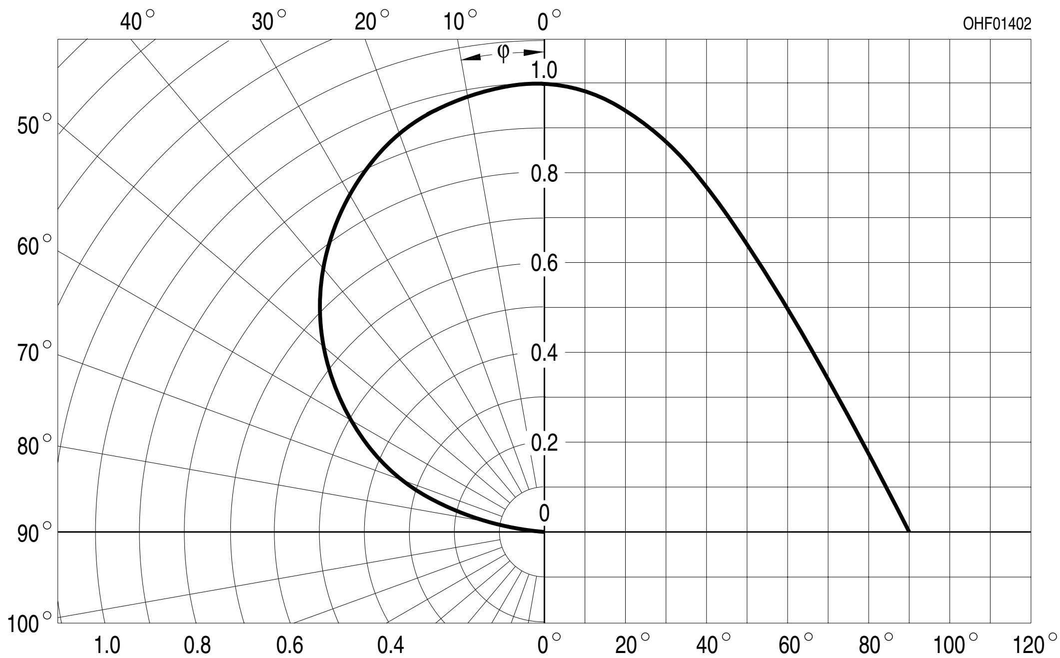
Relative Spectral Sensitivity [2), 3)]

$S_{rel} = f(\lambda)$



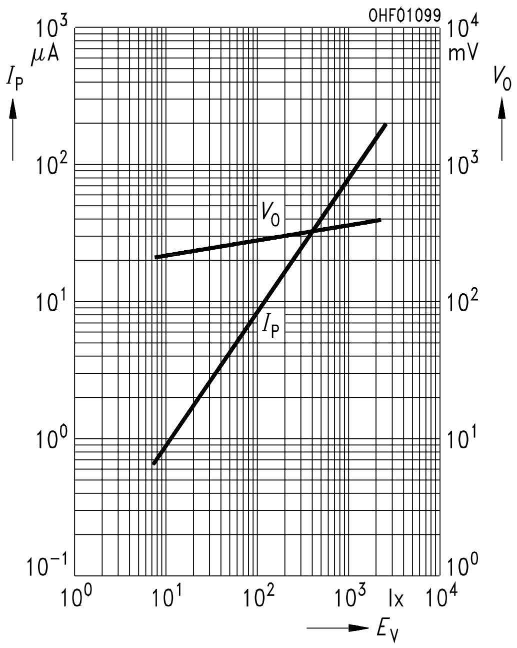
Directional Characteristics [2), 3)]

$S_{rel} = f(\varphi)$



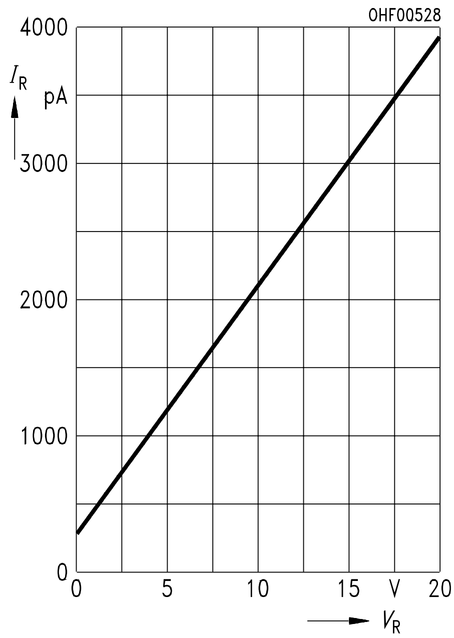
Photocurrent/Open-Circuit Voltage [2), 3)]

I_P (V_R = 5 V) / V_O = f (E_v)



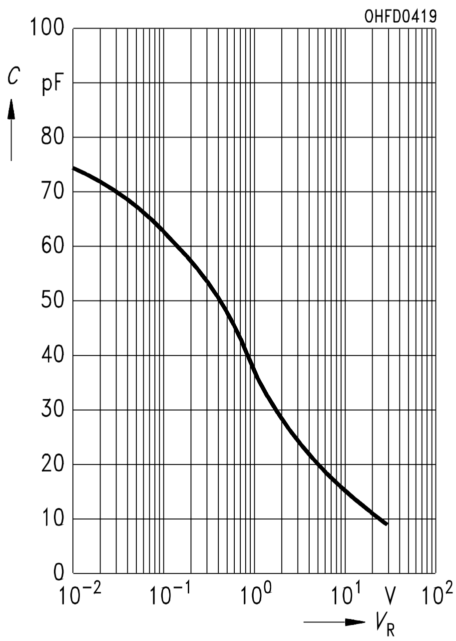
Dark Current [2), 3)]

I_R = f (V_R); E = 0



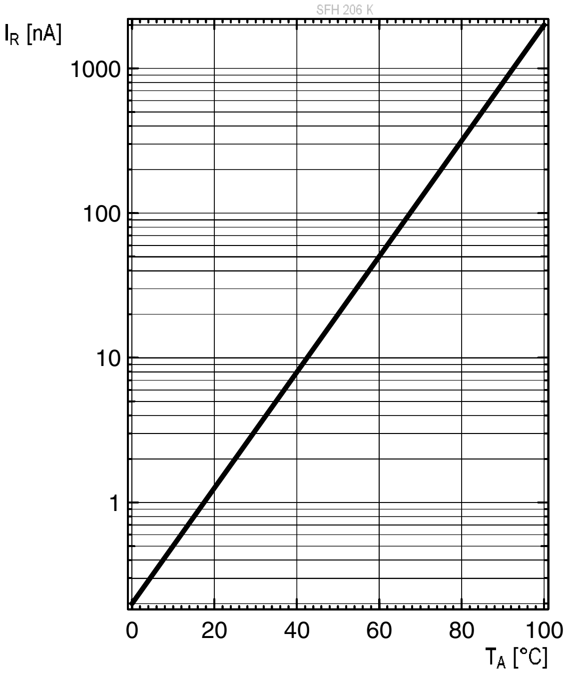
Capacitance [2), 3)]

C = f (V_R); f = 1MHz; E = 0; T_A = 25°C



Dark Current [2)]

$I_R = f(T_A)$; $E = 0$; $V_R = 10$ V



Part Number: L-1503ID High Efficiency Red

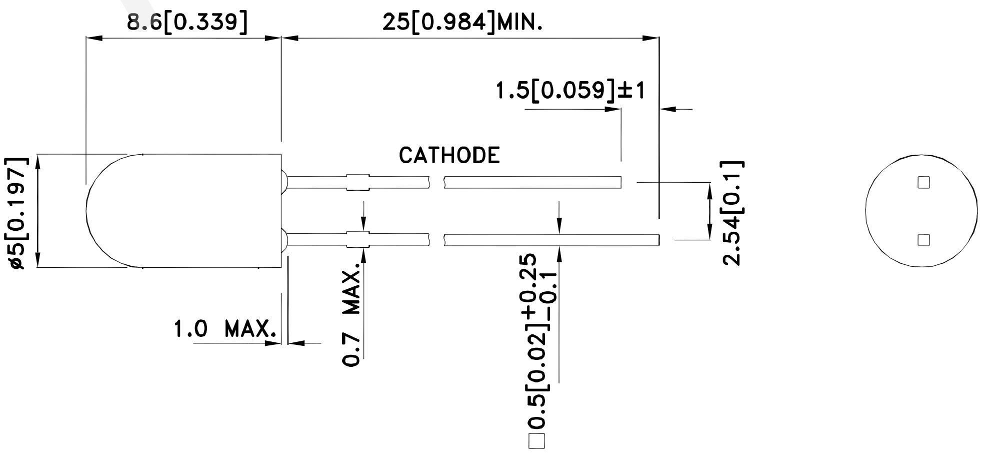
Features

- Low power consumption.
- Versatile mounting on P.C. board or panel.
- T-1 3/4 diameter flangeless package.
- Reliable and rugged.
- RoHS compliant.

Description

The High Efficiency Red source color devices are made with Gallium Arsenide Phosphide on Gallium Phosphide Orange Light Emitting Diode.

Package Dimensions



Notes:
1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) [2] @ 10mA		Viewing Angle [1]
			Min.	Typ.	2θ1/2
L-1503ID	High Efficiency Red (GaAsP/GaP)	Red Diffused	25	50	60°
			*12	*40	

Notes:
1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 of the optical peak value.
2. Luminous intensity/ luminous Flux: +/-15%.
  * Luminous intensity value is traceable to the CIE127-2007 compliant national standards.

Electrical / Optical Characteristics at TA=25°C

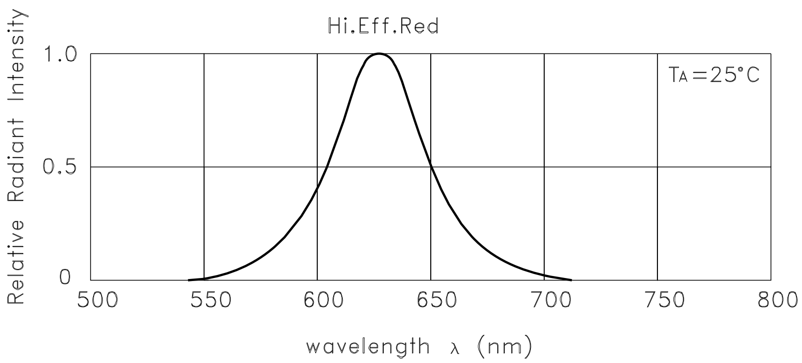
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λpeak	Peak Wavelength	High Efficiency Red	627		nm	I_F=20mA
λD [1]	Dominant Wavelength	High Efficiency Red	617		nm	I_F=20mA
Δλ1/2	Spectral Line Half-width	High Efficiency Red	45		nm	I_F=20mA
C	Capacitance	High Efficiency Red	15		pF	V_F=0V;f=1MHz
V_F [2]	Forward Voltage	High Efficiency Red	2	2.5	V	I_F=20mA
I_R	Reverse Current	High Efficiency Red		10	uA	V_R = 5V

Notes:
1.Wavelength: +/-1nm.
2. Forward Voltage: +/-0.1V.
3. Wavelength value is traceable to the CIE127-2007 compliant national standards.

Absolute Maximum Ratings at TA=25°C

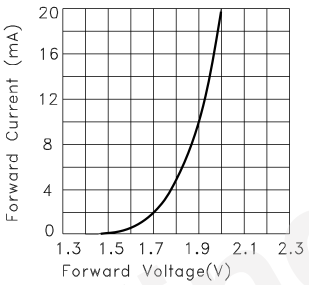
Parameter	High Efficiency Red	Units
Power dissipation	75	mW
DC Forward Current	30	mA
Peak Forward Current [1]	160	mA
Reverse Voltage	5	V
Operating/Storage Temperature	-40°C To +85°C	
Lead Solder Temperature [2]	260°C For 3 Seconds	
Lead Solder Temperature [3]	260°C For 5 Seconds	

Notes:
1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 2mm below package base.
3. 5mm below package base.

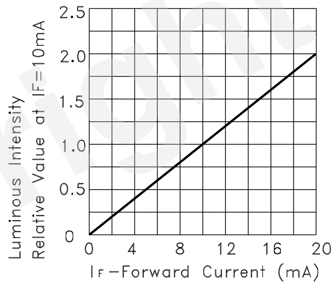


RELATIVE INTENSITY Vs. WAVELENGTH

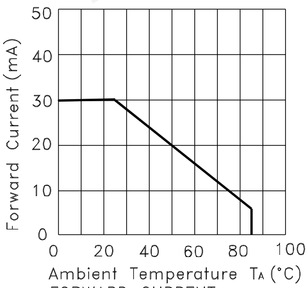
High Efficiency Red L-1503ID



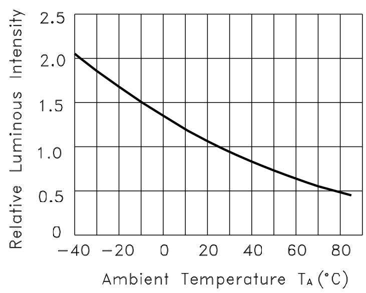
FORWARD CURRENT Vs.
FORWARD VOLTAGE



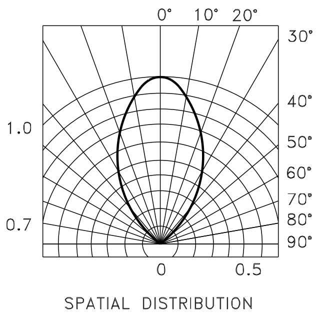
LUMINOUS INTENSITY Vs.
FORWARD CURRENT



FORWARD CURRENT
DERATING CURVE



LUMINOUS INTENSITY Vs.
AMBIENT TEMPERATURE



SPATIAL DISTRIBUTION

SLOS081I – FEBRUARY 1977 – REVISED MAY 2015

TL08xx JFET-Input Operational Amplifiers

1 Features

- Low Power Consumption: 1.4 mA/ch Typical
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias Current: 30 pA Typical
- Low Input Offset Current: 5 pA Typical
- Output Short-Circuit Protection
- Low Total Harmonic Distortion: 0.003% Typical
- High Input Impedance: JFET Input Stage
- Latch-Up-Free Operation
- High Slew Rate: 13 V/μs Typical
- Common-Mode Input Voltage Range Includes V_{CC+}

2 Applications

- Tablets
- White goods
- Personal electronics
- Computers

3 Description

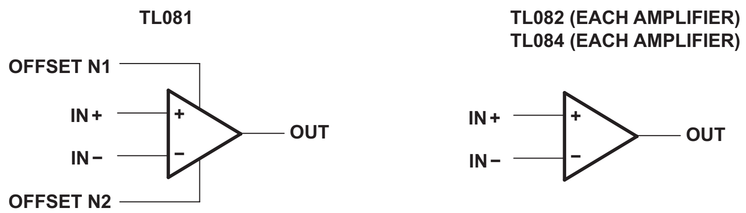
The TL08xx JFET-input operational amplifier family is designed to offer a wider selection than any previously developed operational amplifier family. Each of these JFET-input operational amplifiers incorporates well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit. The devices feature high slew rates, low input bias and offset currents, and low offset-voltage temperature coefficient.

Device Information[1]

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TL084xD	SOIC (14)	8.65 mm × 3.91 mm
TL08xxFK	LCCC (20)	8.89 mm × 8.89 mm
TL084xJ	CDIP (14)	19.56 mm × 6.92 mm
TL084xN	PDIP (14)	19.3 mm × 6.35 mm
TL084xNS	SO (14)	10.3 mm × 5.3 mm
TL084xPW	TSSOP (14)	5.0 mm × 4.4 mm

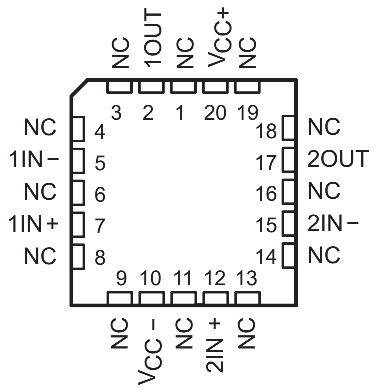
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Schematic Symbol

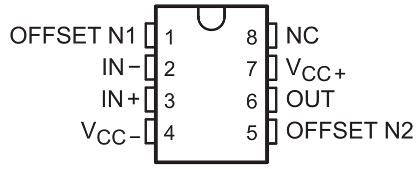


5 Pin Configuration and Functions

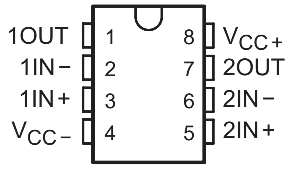
TL082 FK Package
20-Pin LCCC
Top View



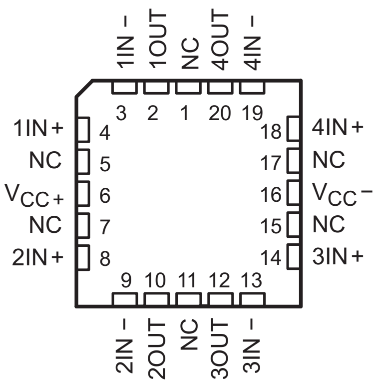
TL081 and TL081x D, P, and PS Package
8-Pin SOIC, PDIP, and SO
Top View



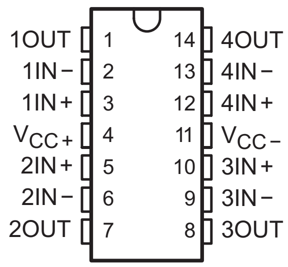
TL082 and TL082x D, JG, P, PS and PW Package
8-Pin SOIC, CDIP, PDIP, SO, and TSSOP
Top View



TL084 FK Package
20-Pin LCCC
Top View



TL084 and TL084x D, J, N, NS and PW Package
14-Pin SOIC, CDIP, PDIP, SO, and TSSOP
Top View



Pin Functions

PIN						I/O	DESCRIPTION
NAME	TL081	TL082		TL084			
	SOIC, PDIP, SO	SOIC, CDIP, PDIP, SO, TSSOP	LCCC	SOIC, CDIP, PDIP, SO, TSSOP	LCCC		
1IN–	—	2	5	2	3	I	Negative input
1IN+	—	3	7	3	4	I	Positive input
1OUT	—	1	2	1	2	O	Output
2IN–	—	6	15	6	9	I	Negative input
2IN+	—	5	12	5	8	I	Positive input
2OUT	—	7	17	7	10	O	Output
3IN–	—	—	—	9	13	I	Negative input
3IN+	—	—	—	10	14	I	Positive input
3OUT	—	—	—	8	12	O	Output
4IN–	—	—	—	13	19	I	Negative input
4IN+	—	—	—	12	18	I	Positive input
4OUT	—	—	—	14	20	O	Output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

				MIN	MAX	UNIT
V_{CC+}	Supply voltage(2)				18	V
V_{CC-}					–18	
V_{ID}	Differential input voltage(3)				±30	V
V_I	Input voltage(2)(4)				±15	V
	Duration of output short circuit(5)			Unlimited		
	Continuous total power dissipation			See *Dissipation Rating Table*		
T_A	Operating free-air temperature		TL08_C TL08_AC TL08_BC	0	70	°C
			TL08_I	–40	85	
			TL084Q	–40	125	
			TL08_M	–55	125	
	Operating virtual junction temperature				150	°C
T_C	Case temperature for 60 seconds	FK package	TL08_M		260	°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	J or JG package	TL08_M		300	°C
T_{stg}	Storage temperature			–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-}.
(3) Differential voltages are at IN+, with respect to IN−.
(4) The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
(5) The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	1000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC+}	Supply voltage		5	15	V
V_{CC-}	Supply voltage		–5	–15	V
V_{CM}	Common-mode voltage		V_{CC-} + 4	V_{CC+} – 4	V
T_A	Ambient temperature	TL08xM	–55	125	°C
		TL08xQ	–40	125	
		TL08xI	–40	85	
		TL08xC	0	70	

6.4 Thermal Information

THERMAL METRIC[1]		TL08xx								UNIT
		D (SOIC)		N (PDIP)	NS (SO)	P (PDIP)	PS (SO)	PW (TSSOP)		
		8 PINS	14 PINS	14 PINS	14 PINS	{PIN COUNT} PINS	{PIN COUNT} PINS	8 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance[2][3]	97	86	76	80	85	95	149	113	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.
(2) Maximum power dissipation is a function of $T_{J(max)}$, $R_{\theta JA}$, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_{J(max)} - T_A) / R_{\theta JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
(3) The package thermal impedance is calculated in accordance with JESD 51-7.

6.5 Electrical Characteristics for TL08xC, TL08xxC, and TL08xI

$V_{CC\pm}$ = ±15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A[1]	TL081C, TL082C, TL084C			TL081AC, TL082AC, TL084AC			TL081BC, TL082BC, TL084BC			TL081I, TL082I, TL084I			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO}	Input offset voltage	V_O = 0, R_S = 50 Ω	25°C		3	15		3	6		2	3		3	6	mV
			Full range			20			7.5			5			9	
α_{VIO}	Temperature coefficient of input offset voltage	V_O = 0, R_S = 50 Ω	Full range		18			18			18			18		μV/°C
I_{IO}	Input offset current[2]	V_O = 0	25°C		5	200		5	100		5	100		5	100	pA
			Full range			2			2			2			10	nA
I_{IB}	Input bias current[2]	V_O = 0	25°C		30	400		30	200		30	200		30	200	pA
			Full range			10			7			7			20	nA
V_{ICR}	Common-mode input voltage range		25°C	±11	–12 to 15		±11	–12 to 15		±11	–12 to 15		±11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	R_L = 10 kΩ	25°C	±12	±13.5		±12	±13.5		±12	±13.5		±12	±13.5		V
		R_L ≥ 10 kΩ	Full range	±12			±12			±12			±12			
		R_L ≥ 2 kΩ		±10	±12		±10	±12		±10	±12		±10	±12		
A_{VD}	Large-signal differential voltage amplification	V_O = ±10 V, R_L ≥ 2 kΩ	25°C	25	200		50	200		50	200		50	200		V/mV
			Full range	15			15			25			25			
B_1	Unity-gain bandwidth		25°C		3			3			3			3		MHz
r_i	Input resistance		25°C		10^{12}			10^{12}			10^{12}			10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}$min, V_O = 0, R_S = 50 Ω	25°C	70	86		75	86		75	86		75	86		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	V_{CC} = ±15 V to ±9 V, V_O = 0, R_S = 50 Ω	25°C	70	86		80	86		80	86		80	86		dB

(1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified. Full range for T_A is 0°C to 70°C for TL08_C, TL08_AC, TL08_BC and –40°C to 85°C for TL08_I.
(2) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in Figure 13. Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

Electrical Characteristics for TL08xC, TL08xxC, and TL08xI (continued)

$V_{CC\pm}$ = ±15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A(1)	TL081C, TL082C, TL084C			TL081AC, TL082AC, TL084AC			TL081BC, TL082BC, TL084BC			TL081I, TL082I, TL084I			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
I_{CC}	Supply current (each amplifier)	V_O = 0, No load	25°C		1.4	2.8		1.4	2.8		1.4	2.8		1.4	2.8	mA
V_{O1}/V_{O2}	Crosstalk attenuation	A_{VD} = 100	25°C		120			120			120			120		dB

6.6 Electrical Characteristics for TL08xM and TL084x

$V_{CC\pm}$ = ±15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS(1)	T_A	TL081M, TL082M			TL084Q, TL084M			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO}	Input offset voltage	V_O = 0, R_S = 50 Ω	25°C		3	6		3	9	mV
			Full range			9			15	
α_{VIO}	Temperature coefficient of input offset voltage	V_O = 0, R_S = 50 Ω	Full range		18			18		μV/°C
I_{IO}	Input offset current(2)	V_O = 0	25°C		5	100		5	100	pA
			125°C			20			20	nA
I_{IB}	Input bias current(2)	V_O = 0	25°C		30	200		30	200	pA
			125°C			50			50	nA
V_{ICR}	Common-mode input voltage range		25°C	±11	–12 to 15		±11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	R_L = 10 kΩ	25°C	±12	±13.5		±12	±13.5		V
		R_L ≥ 10 kΩ	Full range	±12			±12			
		R_L ≥ 2 kΩ		±10	±12		±10	±12		
A_{VD}	Large-signal differential voltage amplification	V_O = ±10 V, R_L ≥ 2 kΩ	25°C	25	200		25	200		V/mV
			Full range	15			15			
B_1	Unity-gain bandwidth		25°C		3			3		MHz
r_i	Input resistance		25°C		10^{12}			10^{12}		Ω
CMRR	Common-mode rejection ratio	V_{IC} = V_{ICR}min, V_O = 0, R_S = 50 Ω	25°C	80	86		80	86		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	V_{CC} = ±15 V to ±9 V, V_O = 0, R_S = 50 Ω	25°C	80	86		80	86		dB
I_{CC}	Supply current (each amplifier)	V_O = 0, No load	25°C		1.4	2.8		1.4	2.8	mA
V_{O1}/V_{O2}	Crosstalk attenuation	A_{VD} = 100	25°C		120			120		dB

(1) All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified.
(2) Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in Figure 13. Pulse techniques must be used that maintain the junction temperatures as close to the ambient temperature as possible.

6.7 Operating Characteristics

$V_{CC\pm}$ = ±15 V, T_A= 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	V_I = 10 V, R_L = 2 kΩ, C_L = 100 pF, See Figure 19	8(1)	13		V/μs
		V_I = 10 V, R_L = 2 kΩ, C_L = 100 pF, T_A = − 55°C to 125°C, See Figure 19	5(1)			

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

6.9 Typical Characteristics

Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices. The Figure numbers referenced in the following graphs are located in *Parameter Measurement Information*.

Table 1. Table of Graphs

			Figure
V_{OM}	Maximum peak output voltage	versus Frequency versus Free-air temperature versus Load resistance versus Supply voltage	Figure 1, Figure 2, Figure 3 Figure 4 Figure 5 Figure 6
A_{VD}	Large-signal differential voltage amplification	versus Free-air temperature versus Load resistance	Figure 7 Figure 8
	Differential voltage amplification	versus Frequency with feed-forward compensation	Figure 9
P_D	Total power dissipation	versus Free-air temperature	Figure 10
I_{CC}	Supply current	versus Free-air temperature versus Supply voltage	Figure 11 Figure 12
I_{IB}	Input bias current	versus Free-air temperature	Figure 13
	Large-signal pulse response	versus Time	Figure 14
V_O	Output voltage	versus Elapsed time	Figure 15
CMRR	Common-mode rejection ratio	versus Free-air temperature	Figure 16
V_n	Equivalent input noise voltage	versus Frequency	Figure 17
THD	Total harmonic distortion	versus Frequency	Figure 18

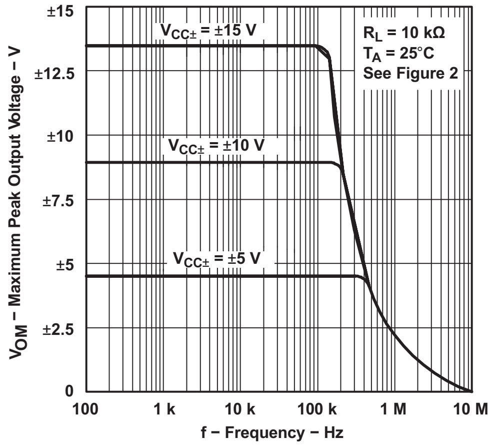


Figure 1. Maximum Peak Output Voltage vs Frequency

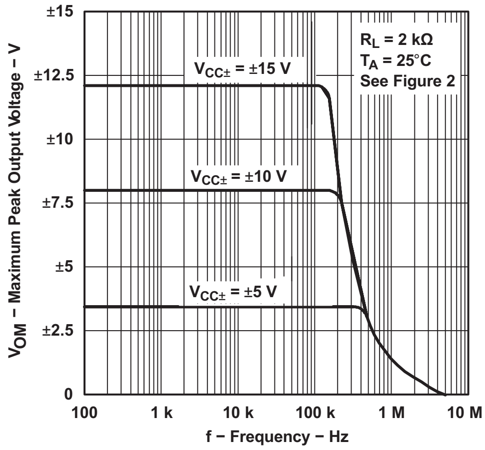


Figure 2. Maximum Peak Output Voltage vs Frequency

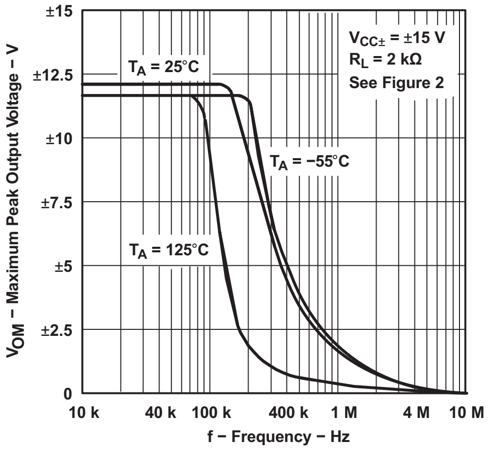


Figure 3. Maximum Peak Output Voltage vs Frequency

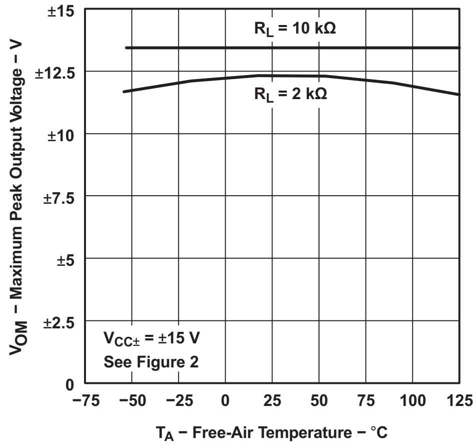


Figure 4. Maximum Peak Output Voltage vs Free-Air Temperature

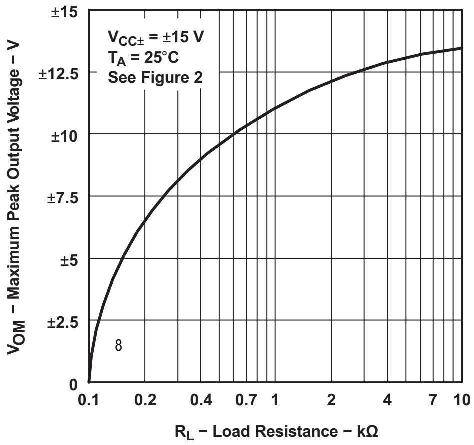


Figure 5. Maximum Peak Output Voltage vs Load Resistance

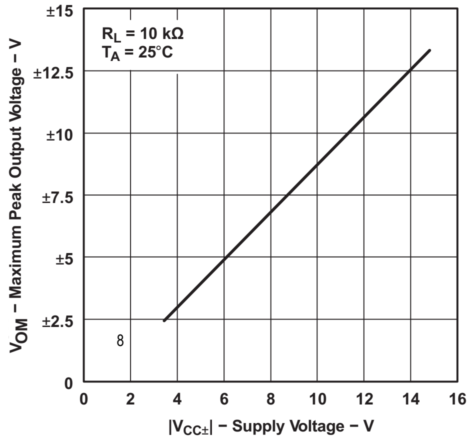


Figure 6. Maximum Peak Output Voltage vs Supply Voltage

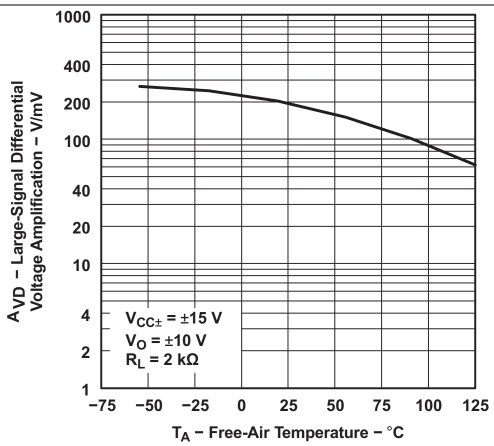


Figure 7. Large-Signal Differential Voltage Amplification vs Free-Air Temperature

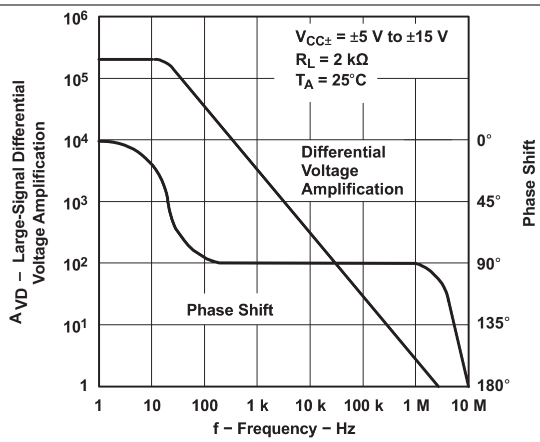


Figure 8. Large-Signal Differential Voltage Amplification and Phase Shift vs Frequency

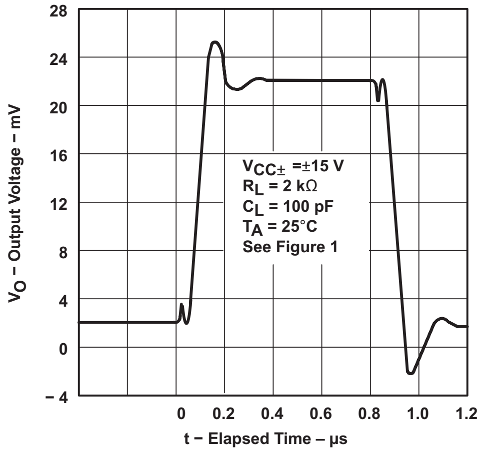


Figure 15. Output Voltage vs Elapsed Time

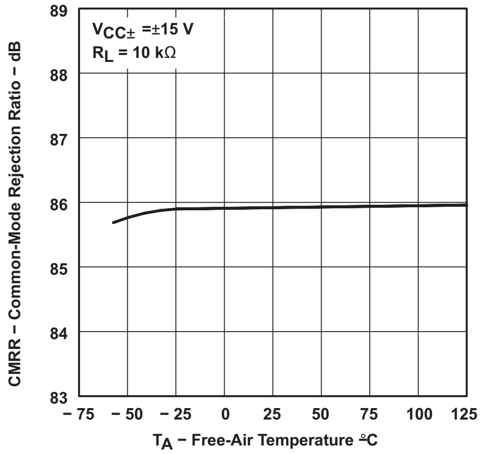


Figure 16. Common-Mode Rejection Ratio vs Free-Air Temperature

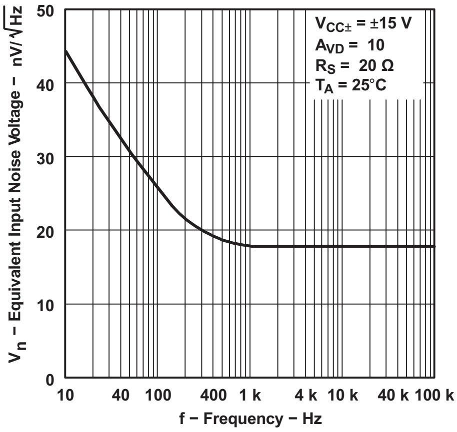


Figure 17. Equivalent Input Noise Voltage vs Frequency

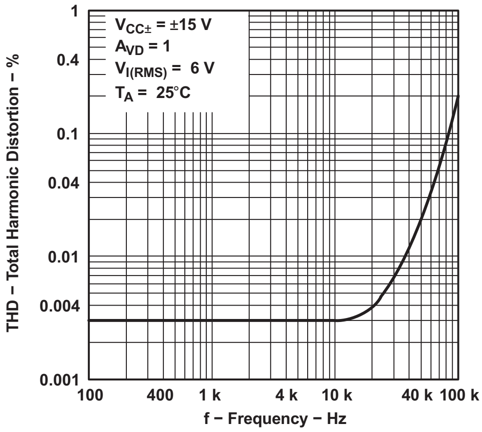


Figure 18. Total Harmonic Distortion vs Frequency

7 Parameter Measurement Information

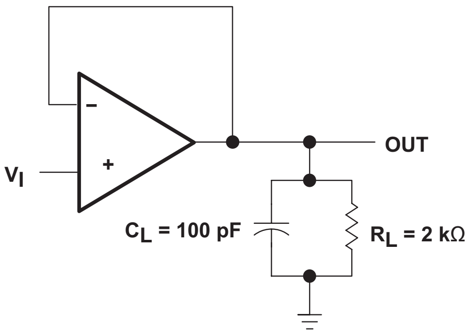


Figure 19. Test Figure 1

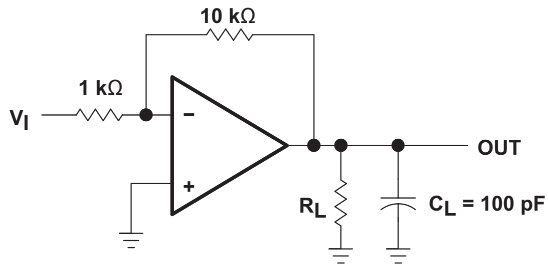


Figure 20. Test Figure 2

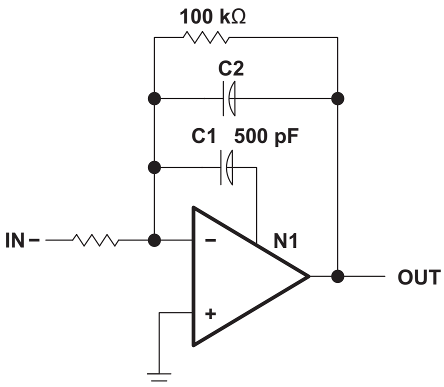


Figure 21. Test Figure 3

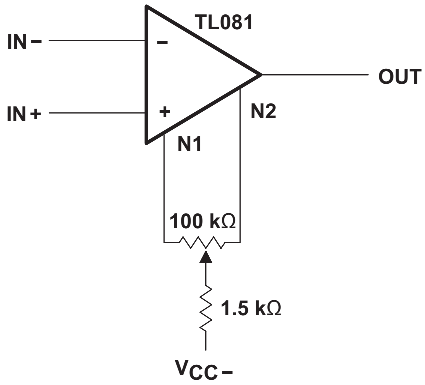


Figure 22. Test Figure 4